

SCRs

1.6 Amp, Planar

ID200-ID203
ID300-ID301

FEATURES

- Voltage Rating: to 200V
- Max. Gate Trigger Current: 200 μ A
- Hermetically Sealed Metal Can
- Planar Passivated Construction

DESCRIPTION

This Data Sheet describes Microsemi's line of hermetically sealed industrial SCRs designed for high-voltage, medium-current control applications. The Series is packaged in a TO-39 metal case with Microsemi's unique oxide passivated junctions to ensure reliability and parameter stability. Typical applications include relay equipment, motor controls, process controllers and pulse generators.

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ABSOLUTE MAXIMUM RATINGS

	ID200	ID201	ID202	ID203	ID300	ID301
Repetitive Peak Off-State Voltage, V_{DRM}	50V	100V	150V	200V	300V	400V
Repetitive Peak Reverse Voltage, V_{RRM}	50V	100V	150V	200V	300V	400V
Non-Repetitive Peak Reverse Voltage, V_{RSM} (<5ms)	75V	150V	225V	300V	400V	500V
On-State Current, $I_{T(RMS)}$						
70°C Case	1.6A					
75°C Ambient	450mA					
Peak One Cycle Surge (Non-Repetitive) On-State Current, I_{TSM}	15A					
Repetitive Peak On-State Current, I_{TRM}	up to 30A					
Rate of Rise of On-State Current, di/dt	100A/ μ s					
I^2t (for times > 1.5 ms)	0.83A ² s					
Peak Gate Current, I_{GM}	250mA					
Average Gate Current, $I_{G(AV)}$	25mA					
Reverse Gate Voltage, V_{GR}	6V					
Storage Temperature Range	-65°C to +150°C					
Operating Temperature Range	-40°C to +110°C					

MECHANICAL SPECIFICATIONS

	ins.	mm.
A	.305-.335	7.75-8.51
B	.315-.370	8.51-9.40
C	.240-.260	6.35-6.60
D	.010-.030	.25-.76
E	.5 MIN.	12.70 MIN.
F	.017 ± .002 .001	.432 ± .051 .025
G	.200	5.08
H	.100	2.54
J	.031 ± .003	.79 ± .08
K	.029-.045	.74-1.14
L	.100	2.54

TO-205AD (TO-39)

ELECTRICAL SPECIFICATIONS (at 25°C unless noted)

Test	Symbol	Min.	Typ.	Max.	Units	Test Conditions
Off-State Current	I_{DRM}	—	—	10 100	μA μA	$V_{DRM} = \text{Rating}, R_{GK} = 1K, T = 25^{\circ}C$ $V_{DRM} = \text{Rating}, R_{GK} = 1K, T = 110^{\circ}C$
Reverse Current	I_{RRM}	—	—	10 100	μA μA	$V_{RRM} = \text{Rating}, R_{GK} = 1K, T = 25^{\circ}C$ $V_{RRM} = \text{Rating}, R_{GK} = 1K, T = 110^{\circ}C$
Gate Trigger Current	I_{GT}	—	—	200 500	μA μA	$V_D = 5V, R_{GS} = 10K, T = 25^{\circ}C$ $V_D = 5V, R_{GS} = 10K, T = -40^{\circ}C$
On-State Voltage	V_{GT}	0.4 0.5 0.2	0.52 0.7 —	0.8 1.0 —	V V V	$V_D = 5V, R_{GS} = 100\Omega, T = 25^{\circ}C$ $V_D = 3V, R_{GS} = 100\Omega, T = -40^{\circ}C$ $V_D = 5V, R_{GS} = 100\Omega, T = 110^{\circ}C$
Peak On — Voltage	V_{TM}	—	—	2.2	V	$I_T = 4 \text{ Amp Pulse}, T = 25^{\circ}C$
Holding Current	I_H	0.3 0.4 0.2	0.7 — —	3.0 6.0 —	mA mA mA	$R_{GK} = 1K, T = 25^{\circ}C$ $R_{GK} = 1K, T = -40^{\circ}C$ $R_{GK} = 1K, T = 110^{\circ}C$
Off-State Voltage — Critical Rate of Rise	dv/dt	—	20	—	V/ μs	$V_{DRM} = \text{Rated}, R_{GK} = 1K, T = 110^{\circ}C$
Turn-on Time	t_{on}	—	1.0	—	μs	$I_G = 10mA, I_T = I_A, V_D = 30V, T = 25^{\circ}C$
Circuit Commutated Turn-off Time	t_q	—	—	40	μs	$I_T = I_R = 1A, R_{GK} = 1K, T = 25^{\circ}C$

Note: Blocking voltage ratings apply over the full operating temperature range, provided the gate is connected to the cathode through a resistor, 1000 ohms or smaller, or other adequate bias is used.